

HIGH-SPEED 128K x 9 SYNCHRONOUS PIPELINED DUAL-PORT STATIC RAM

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Features

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - *Commercial: 7.5/9/12ns (max.)*
 - Industrial: 9ns (max.)
- Low-power operation
 - IDT709199L
 - Active: 1.2W (typ.)
 - Standby: 2.5mW (typ.)
- Flow-Through or Pipelined output mode on either Port via the FT/PIPE pins
- Counter enable and reset features
- * Dual chip enables allow for depth expansion without

Functional Block Diagram

- additional logic Full synchronous operation on both ports
- 4ns setup to clock and Ons hold on all control, data, and address inputs
- Data input, address, and control registers
- Fast 7.5ns clock to data out in the Pipelined output mode
- Self-timed write allows fast cycle time
- 12ns cycle time, 83MHz operation in Pipelined output mode
- TTL- compatible, single 5V (±10%) power supply
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
 - Available in a 100-pin Thin Quad Flatpack (TQFP) package



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High-Speed 128K x 9 Synchronous Pipelined Dual-Port Static RAM

Description

The IDT709199 is a high-speed 128K x 9 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT709199 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by $\overline{CE}o$ and CE_1 , permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 1.2W of power.



Pin Configurations^(1,2,3)

- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground.
- 3. Package body is approximately 14mm x 14mm x 1.4mm
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names
CEOL, CE1L	$\overline{\text{CE}}$ OR, CE1R	Chip Enables
R/WL	R/WR	Read/Write Enable
ŌĒL	ŌĒR	Output Enable
A0L - A16L	Aor - A16r	Address
I/Ool - I/O8l	1/Oor - 1/O8r	Data Input/Output
CLKL	CLKr	Clock
ADSL	ADSR	Address Strobe
	CNTEN R	Counter Enable
CNTRST L		Counter Reset
FT/PIPEL	FT /PIPER	Flow-Through/Pipeline
V	сс	Power
G	ND	Ground

4847 tbl 01

Truth Table I—Read/Write and Enable Control^(1,2,3)

ŌĒ	CLK	Ē₽	CE1	R/W	I/O0-8	Mode
Х	Ŷ	Н	Х	Х	High-Z	Deselected—Power Down
Х	Ŷ	Х	L	Х	High-Z	Deselected—Power Down
Х	Ŷ	L	Н	L	DATAIN	Write
L	Ŷ	L	Н	Н	DATAOUT	Read
Н	Х	L	Н	Х	High-Z	Outputs Disabled
						4847 tbl 02

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care. 2. \overline{ADS} , \overline{CNTEN} , \overline{CNTRST} = X.

3. OE is an asynchronous input signal.

Address	Previous Address	Addr Used	CLK	ADS	CNTEN	CNTRST	I/O ⁽³⁾	Mode
Х	Х	0	←	Х	Х	L	Dvo(0)	Counter Reset to Address 0
An	Х	An	Ŷ	L ⁽⁴⁾	Х	Н	DVO(n)	External Address Utilized
An	Ар	Ар	Ŷ	Н	Н	Н	D⊮O(p)	External Address Blocked—Counter Disabled (Ap reused)
Х	Ар	Ap + 1	\uparrow	Н	L ⁽⁵⁾	Н	DI/O(p+1)	Counter Enable—Internal Address Generation

Truth Table II—Address Counter Control^(1,2,6)

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care. 2. \overline{CE}_0 and \overline{OE} = VIL; CE1 and R/W = VIH.

3. Outputs configured in Flow-Through Output mode: if outputs are in Pipelined mode the data out will be delayed by one cycle.

ADS is independent of all other signals including CE₀ and CE1.
 The address counter advances if CNTEN = <u>VIL</u> on the rising edge of CLK, regardless of all other signals including CE₀ and CE1.

6. While an external address is being loaded (ADS = VIL), RIW = VIH is recommended to ensure data is not written arbitrarily.

4847 tbl 03

High-Speed 128K x 9 Synchronous Pipelined Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Recommended Operating Recommen Temperature and Supply Voltage Conditions

Grade	Ambient Temperature ⁽²⁾	GND	Vcc
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
Tbias	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
Ιουτ	DC Output Current	50	mA

NOTES:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

 VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
Vih	Input High Voltage	2.2	_	6.0 ⁽¹⁾	V
Vil	Input Low Voltage	-0.5 ⁽²⁾	_	0.8	V

NOTES:

4847 tbl 04

4847 tbl 06

1. VTERM must not exceed Vcc + 10%.

2. VIL \geq -1.5V for pulse width less than 10ns.

Capacitance⁽¹⁾

 $(TA = +25^{\circ}C, f = 1.0MHz)$

Symbol	Parameter	Conditions ⁽²⁾	Мах.	Unit
Cin	Input Capacitance	VIN = 3dV	9	рF
Cout ⁽³⁾	Output Capacitance	Vout = 3dV	10	рF

NOTES:

- These parameters are determined by device characterization, but are not production tested.
- 2. 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.
- 3. COUT also references CI/O.

DC Electrical Characteristics Over the Operating Temperature Supply Voltage Range (Vcc = 5.0V ± 10%)

			709 ⁻		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Lı	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, VIN = 0V to Vcc		5	μA
Ilo	Output Leakage Current	$\overline{CE}_0 = V_{IH} \text{ or } CE_1 = V_{IL}, V_{OUT} = 0V \text{ to } V_{CC}$		5	μA
Vol	Output Low Voltage	lol = +4mA		0.4	V
Vон	Output High Voltage	Юн = -4mA	2.4	1	V

NOTE:

1. At Vcc \leq 2.0V input leakages are undefined.

4847 tbl 05

4847 tbl 07

4847 tbl 08

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽³⁾ ($Vcc = 5V \pm 10\%$)

					7091 ⁽ Com'l		7091 ⁴ Coi & I	n'l	70919 Com'l	9L12 Only	
Symbol	Parameter	Test Condition	Versi	on	Тур. ⁽⁴⁾	Мах.	Тур. ⁽⁴⁾	Max.	Тур. ⁽⁴⁾	Мах.	Unit
Icc	Dynamic Operating Current	CEL and CER= VIL	COM'L	L	275	465	250	400	230	355	mA
	(Both Ports Active)	Outputs Disabled f = fMAX ⁽¹⁾	IND	L		_	300	430			
ISB1	Standby Current	Both Ports - TTL $f = fMAX^{(1)}$	COM'L	L	95	150	80	135	70	110	mA
	Level Inputs)		IND	L			9 5	160			
ISB2	Standby Current (One Port - TTL	$\label{eq:constraint} \begin{array}{ c c } \overline{C}\overline{E}^*A^* = V \mathbb{I}_{L} \mbox{ and } \\ \overline{C}\overline{E}^*B^* = V \mathbb{H}^{(3)} \\ \mbox{ Active Port Outputs } \\ \mbox{ Disabled, } f=fMAX^{(1)} \end{array}$	COM'L	L	200	295	175	275	150	240	mA
	Level Inputs)		IND	L			195	295			
ISB3	Full Standby Current	Both Ports CER and	COM'L	L	0.5	3.0	0.5	3.0	0.5	3.0	mA
	(Both Ports - CMOS Level Inputs)		IND	L			0.5	6.0			
ISB4	Full Standby Current	$\overline{CE}^{"A"} \leq 0.2V$ and	COM'L	L	190	290	170	270	140	225	mA
	(One Port - CMOS Level Inputs)	One Port - $\overline{CE}B^* \ge VCC - 0.2V^{(5)}$	IND	L			190	290			

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NOTES:

1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcvc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

4. Vcc = 5V, TA = 25°C for Typ, and are not production tested. Icc cc(f=0) = 150mA (Typ).

5. $\overline{CE}x = VIL$ means $\overline{CE}0x = VIL$ and CE1x = VIH $\overline{CE}x = VIH$ means $\overline{CE}ox = VIH$ or CE1x = VIL

 $\label{eq:constraint} \begin{array}{|c|c|c|c|c|} \hline \hline CEx \leq 0.2V \mbox{ means } \hline CEox \leq 0.2V \mbox{ and } CE1x \geq Vcc \mbox{ - } 0.2V \mbox{ means } \hline CEox \geq Vcc \mbox{ - } 0.2V \mbox{ or } CE1x \leq 0.2V \end{tabular}$

"X" represents "L" for left port or "R" for right port.

IDT709199L High-Speed 128K x 9 Synchronous Pipelined Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

 893Ω

5pF*

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1,2 and 3

4847 tbl 10



40 60 80 100 120 140 160 180 200 2Ø Capacitance (pF) -1 4847 drw 06

Figure 3. Typical Output Derating (Lumped Capacitive Load).

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AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)⁽³⁾ (Vcc = $5V \pm 10\%$, TA = 0°C to +70°C)

			199L7 I Only	Co	99L9 m'l Ind	709199L12 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	22		25	_	30		ns
tcyc2	Clock Cycle Time (Pipelined) ⁽²⁾	12		15		20	—	ns
tCH1	Clock High Time (Flow-Through) ⁽²⁾	7.5		12		12	-	ns
tCL1	Clock Low Time (Flow-Through) ⁽²⁾	7.5		12		12		ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	5	_	6	_	8	_	ns
tCL2	Clock Low Time (Pipelined) ⁽²⁾	5		6	_	8	—	ns
tR	Clock Rise Time		3		3		3	ns
tr	Clock Fall Time		3		3		3	ns
tsa	Address Setup Time	4		4		4	—	ns
tha	Address Hold Time	0		1		1		ns
tsc	Chip Enable Setup Time	4		4		4		ns
tнc	Chip Enable Hold Time	0		1		1		ns
tsw	R/W Setup Time	4		4		4		ns
thw	R/W Hold Time	0		1		1		ns
tsp	Input Data Setup Time	4		4		4		ns
thd	Input Data Hold Time	0		1		1		ns
tsad	ADS Setup Time	4		4		4		ns
thad	ADS Hold Time	0		1		1		ns
tscn	CNTEN Setup Time	4		4		4		ns
then	CNTEN Hold Time	0		1		1		ns
t SRST	CNTRST Setup Time	4		4		4	—	ns
thrst	CNTRST Hold Time	0		1		1	_	ns
toe	Output Enable to Data Valid		9		12		12	ns
tolz	Output Enable to Output Low-Z ⁽¹⁾	2		2		2		ns
tонz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽²⁾		18		20		25	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾		7.5		9		12	ns
tDC	Data Output Hold After Clock High	2		2		2		ns
tскнz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	ns
tcklz	Clock High to Output Low-Z ⁽¹⁾	2		2		2	_	ns
Port-to-Port D	Delay	•						•
tcwdd	Write Port Clock High to Read Data Delay	_	28		35		40	ns
tccs	Clock-to-Clock Setup Time		10	1	15		15	ns

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed by device characterization, but is not production tested.

2. The Pipelined output parameters (tcvc2, tcD2) to either the Left or Right ports when FT/PIPE = VIH. Flow-Through parameters (tcvc1, tcD1) apply when FT/PIPE = VIL for that port.

3. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE), FT/PIPER and FT/PIPEL.

Timing Waveform of Read Cycle for Flow-Through Output (FT/PIPE"x" = VIL)^(3,6) tCYC1 🗕 tCH1 — tCL1 CLK \overline{CE}_0 tsc tsc tHC (4) CE1 R/W tsw tΗW tSA tha ADDRESS⁽⁵⁾ An An + 1 An + 2 An + 3 **t**DC tскнz (1)_ tCD Qn + 2 DATAOUT Qn Qn + 1 • tCKLZ (1)_ tonz⁽¹⁾ tDC tolz (1) $\overline{OE}^{(2)}$ tOE 4847 drw 07

Timing Waveform of Read Cycle for Pipelined Operation $(FT/PIPE"x" = VIH)^{(3,6)}$



- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. ADS = VIL, CNTEN and CNTRST = VIH.
- 4. The output is disabled (High-Impedance state) by $\overline{CE}_0 = V_{IH}$ or CE₁ = V_{IL} following the next rising edge of the clock. Refer to Truth Table 1.
- 5. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers
- are for reference use only."X" here denotes Left or Right port. The diagram is with respect to that port.

Timing Waveform of a Bank Select Pipelined Read^(1,2)



Timing Waveform of Write with Port-to-Port Flow-Through Read^(4,5,7)



- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT709199 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. \overline{OE} and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/W, \overline{CNTEN} , and \overline{CNTRST} = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. \overline{CE}_0 and $\overline{ADS} = VIL$; CE1, \overline{CNTEN} , and $\overline{CNTRST} = VIH$.
- 5. $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to.
- If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwbb.
 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcb1. tcwbb does not apply in this case.
- 7. All timing is the same for both Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite from Port "A".



Timing Waveforn of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽³⁾



- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- CEo and ADS = VIL; CE1, CNTEN, and CNTRST = VIH. "NOP" is "No Operation".
 Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.



Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** Controlled)⁽³⁾



- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance is determined by the previous cycle control signals.
- 3. CEo and ADS = VIL; CE1, CNTEN, and CNTRST = VIH. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾



 $Timing\,Waveform\,of\,Flow-Through\,Read\,with\,Address\,Counter\,Advance^{(1)}$



NOTES:

1. \overline{CE}_0 and $\overline{OE} = VIL$; CE1, R/ \overline{W} , and $\overline{CNTRST} = VIH$.

2. If there is no address change via $\overline{ADS} = VIL$ (loading a new address) or $\overline{CNTEN} = VIL$ (advancing the address), i.e. $\overline{ADS} = VIH$ and $\overline{CNTEN} = VIH$, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance (Flow-Through or Pipelined Outputs)⁽¹⁾



Timing Waveform of Counter Reset (Pipelined Outputs)⁽²⁾



- 1. $\overline{CE_0}$ and $R/W = V_{IL}$; CE1 and $\overline{CNTRST} = V_{IH}$.
- 2. $\overline{CE}_0 = VIL; CE_1 = VIH.$
- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
 Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1' Address is written to during this cycle.

High-Speed 128K x 9 Synchronous Pipelined Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

A Functional Description

The IDT709199 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

 $\overline{CE}_0 = V_{IH}$ or CE1 = VIL for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT709199's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{CE}_0 = V_{IL}$ and CE1 = VIH to reactivate the outputs.

Depth and Width Expansion

The IDT709199 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The 709199 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 18-bit or wider applications.



Figure 4. Depth and Width Expansion with IDT709199

Ordering Information



NOTE:

1. Industrial temperature range is available.

For other speeds, packages and powers contact your sales office.

Datasheet Document History

9/30/99: 11/10/99:		lic Release I IDT logo					
12/22/99:	Page 1 Added missing diamond						
1/5/01:	Page 3	Changed information in Truth Table II					
	Page 4	Increased storage temperature parameter					
		Clarified TA parameter					
	Page 5	DC Electrical parameters-changed wording from "open" to "disabled"					
		Put overbar on CE in notes					
	Changed ±200mV to 0mV in notes						
	Deleted Preliminary						
10/19/01:	Page 2 Added date revision for pin configuration						
	Page 5 &	7 Added Industrial temp to column heading and values for 9ns speed to DC & AC Electrical Characteristics					
	Page 15 Added Industrial temp offering to 9ns ordering information						
	Page 4, 5	& 7 Removed Industrial temp footnote from all tables					
	Page 1 &	15 Replace тм logo with ® logo					
01/29/09:	Page 15	Removed "IDT" from orderable part number					

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